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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	
		Filing Date	9/30/2003
		First Named Inventor	Stephen P. Vernon et al
		Group Art Unit	2883
Sheet 1 of 2	Examiner Name	Healy	
		Attorney Docket Number	IL-11011

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document Number	Kind Code ² (if known)	Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
BuH		5,841,931		Foresi et al	Nov. 24, 1998	385 131
BuH		5,354,709		Joseph P. Lorenzo et al	Oct. 11, 1994	437 129
BuH		5,946,562		Yue Kuo	Aug. 31, 1999	438 166
BuH		6204099	B1	Kusumoto et al	March 20, 2001	438 151

FOREIGN PATENT DOCUMENTS							CLASS 5482L.	
Examiner Initials*	Cite- No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
BuH		EP	0567051	B1	Kazuo, Eda	04/20/1993	385	14X

Examiner Signature	B. Healy	Date Considered	3/16/05
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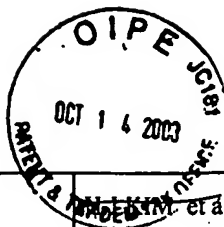
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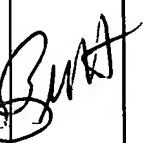
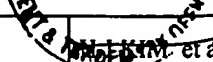
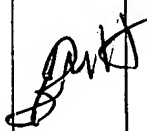
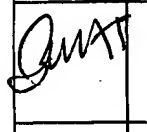
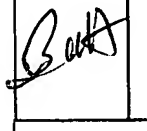
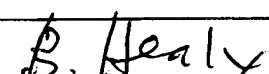
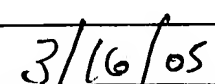
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		Examiner Name	Healy
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T 2
Burt		KJARTAN FAERCH et al	Symmetrical Waveguide Devices Fabricated by Direct UV Writing	IEEE Photonics Technology Letters, Vol. 14, No. 2 February 2002	
Burt		C.M. FORTMANN et al	Hot-wire deposition of photonic-grade amorphous silicon	Thin Solid Films 395 (2001) 142-146	
Burt		GIUSEPPE COCORULLO et al	Amorphous Silicon-Based Guided-Wave Passive and Active Devices for Silicon Integrated Optoelectronics	IEEE Journal of Selected Topics in Quantum Electronics, Vol. 4, No. 6, Nov/Dec 1998	
Burt		MICHAEL O. THOMPSON et al	Melting Temperature and Explosive Crystallization of Amorphous Silicon during Pulsed Laser Irradiation	1984 The American Physical Society Physical Review Letters Vol. 52, Number 26 June 25, 1984 pages 2360-2364	
Burt		OSAMU HANAIZUMI et al	Propagation of light beams along line defects formed in a-Si/SiO2	1999 American Institute of Physics Applied Physics Letters Volume 74, Number 6 pages 777-779	
Burt		S.R. STIFFLER et al	Supercooling and Nucleation of Silicon after Laser Melting	1988 The American Physical Society Physical Review Letters Vol. 60, Number 24, June 1988 pages 2523	



	 KIM et al. kim et al.	New Excimer-laser-crystallization method for producing large-grained and grain boundary-location-controlled Si films for thin film transistors	Appl Phys. Lett 68 (11) March 11, 1996 Pages 1513-1515
	MINGHONG LEE et al	Relationship between fluence gradient and lateral grain growth in spatially controlled excimer laser crystallization of amorphous silicon films	Journal of Applied Physics Vol. 88 Number 9 November 1 2000
	HIROKI TAKAHASHI et al	Influence of Ar impurities on optical refractive index of sputter deposited a-Si films	Journal of Materials Research Vol 12, No. 7 July 1997
	M.H.BRODSKY et al	Structural, Optical, and Electrical Properties of Amorphous Silicon Films	Physical Review B Volume 1, Number 6 March 15, 1970
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